DIODES
INCORPORATED

Green

60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE INTELLIFET MOSFET WITH PROGRAMMABLE CURRENT LIMIT

Product Summary

- Continuous Drain Source Voltage V_{DS} = 60V
- On-State Resistance: 500mΩ
- Nominal Load Current (V_{IN} = 5V): 1.4A
- Clamping Energy: 550mJ

Description

The ZXMS6003G is a self-protected low-side IntelliFET^{TM} MOSFET. It features monolithic overtemperature, overcurrent, overvoltage (active clamp), and ESD protected logic level functionality. It is intended as a general purpose switch with status indication and programmable current limit.

Applications

- Especially Suited for Loads with a High In-Rush Current Such as Lamps and Motors
- All Types of Resistive, Inductive, and Capacitive Loads in Switching Applications
- µC Compatible Power Switch for 12V and 24V DC Applications
- Replaces Electromechanical Relays and Discrete Circuits
- Linear Mode Capability - The current-limiting protection circuitry is designed to deactivate at low V_{DS} in order not to compromise the load current during normal operation. The design max. DC operating current is therefore determined by the thermal capability of the package/board combination rather than by the protection circuitry.
  Note: This does not compromise the product's ability to self-protect during short-circuit load conditions.
- Current Limit is Programmable via an External Resistor R_{PROG} Connected Between Status and IN pins
- Status Pin Voltage Reflects the Gate Drive Applied Internally to the Power MOSFET
- With V_{IN} = 5V and R_{PROG} = 24kΩ:
  - Status Voltage: 5V Indicates Normal Operation
  - Status Voltage: 2V to 3V Indicates the Device is in Current-Limiting Mode
  - Status Voltage <1V Indicates the Device is in Thermal Shutdown

Features and Benefits

- Current Limit Programmable via External Resistor
- Status Pin (Analog Status Indication)
- Logic Level Input
- Short-Circuit Protection with Auto Restart
- Overvoltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- Load Dump Protection (Actively Protects Load)
- High Continuous Current Rating
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
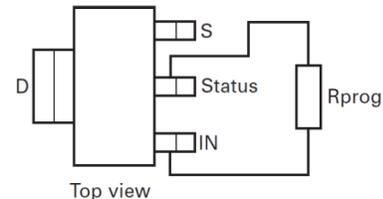
Mechanical Data

- Case: SOT223 (Type DN)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (e3)
- Weight: 0.112 grams (Approximate)

SOT223 (Type DN)

Top View

Note: R_{PROG} must be connected between the Status and IN pins.

Top view

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Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXMS6003GTA	ZXMS6003	7	12	1000 Units

Note: 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information
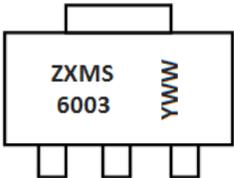
ZXMS
6003   YWW

ZXMS6003 = Product Type Marking Code
YWW = Date Code Marking
Y or $\overline{Y}$ = Last Digit of Year (ex: 8 = 2018)
WW or $\overline{WW}$ = Week Code (01 to 53)

Functional Block Diagram

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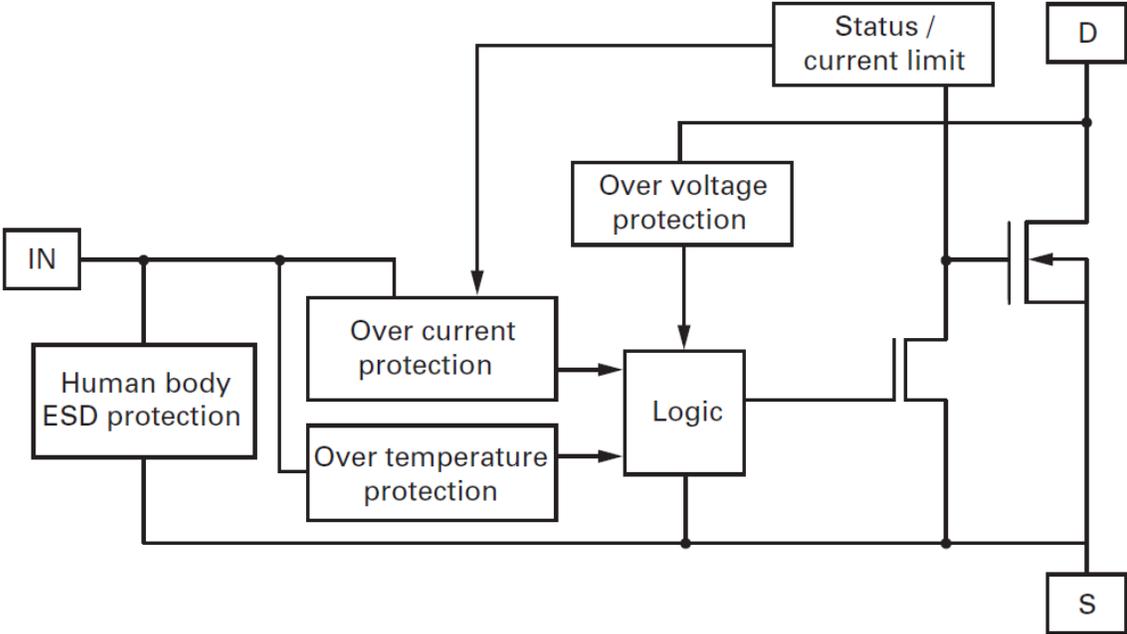
Absolute Maximum Ratings (@T_A = +25°C, unless otherwise stated.)

Parameter	Symbol	Limit	Unit
Continuous Drain-Source Voltage	V_{DS}	60	V
Drain-Source Voltage for Short-Circuit Protection V_{IN} = 5V (Note 5)	$V_{DS(SC)}$	36	V
Drain-Source Voltage for Short-Circuit Protection V_{IN} = 10V (Note 5)	$V_{DS(SC)}$	20	V
Continuous Input Voltage	V_{IN}	-0.2 to +10	V
Peak Input Voltage	V_{IN}	-0.2 to +20	V
Operating Temperature Range	T_J	-40 to +150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Power Dissipation at @T_A = +25°C (Note 6)	P_D	2.5	W
Continuous Drain Current @V_{IN} = 10V; T_A = +25°C (Note 6)	I_D	1.6	A
Continuous Drain Current @V_{IN} = 5V; T_A = +25°C (Note 6)	I_D	1.4	A
Continuous Source Current (Body Diode) (Note 6)	I_S	3	A
Pulsed Source Current (Body Diode) (Note 7)	I_S	8	A
Unclamped Single Pulse Inductive Energy	E_{AS}	550	mJ
Load Dump Protection	$V_{LOADDUMP}$	80	V
Electrostatic Discharge (Human Body Model)	V_{ESD}	4000	V
DIN Humidity Category, DIN 40 040	—	E	—
IEC Climatic Category, DIN IEC 68-1	—	40/150/56	—

Thermal Resistance (@T_A = +25°C, unless otherwise stated.)

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 6)	$R_{\Theta JA}$	50	°C/W
Junction to Ambient (Note 7)	$R_{\Theta JA}$	28	°C/W

Notes: 5. For $I_{D(LIM)}$ < 1.2A (see safe operating area curve).
6. For a device surface mounted on 50mm x 50mm x 1.6mm FR-4 board with a high coverage of single sided 2oz weight copper.
7. For a device surface mounted on FR-4 board and measured at t < = 10s.

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Thermal Characteristics

Safe Operating Area

Safe Operating Area

Transient Thermal Impedance

Pulse Power Dissipation

Derating Curve

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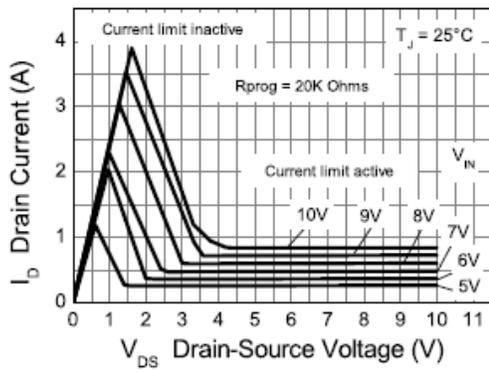
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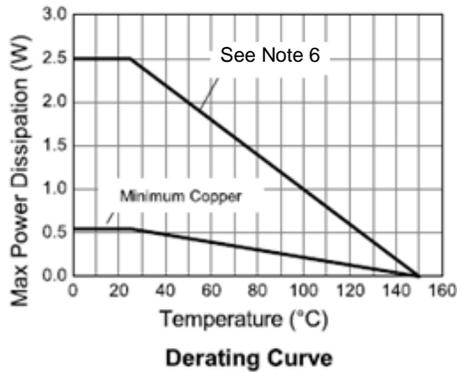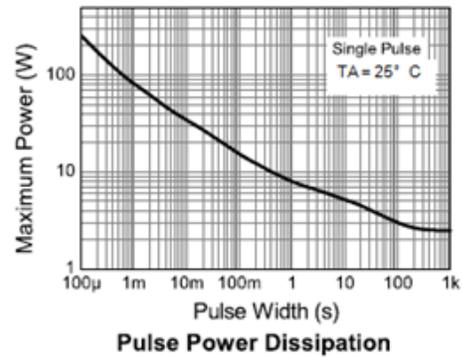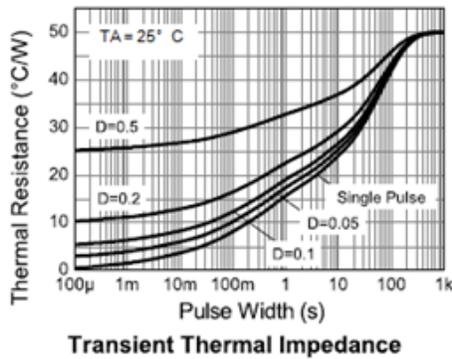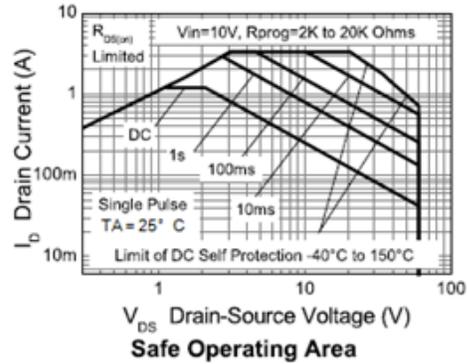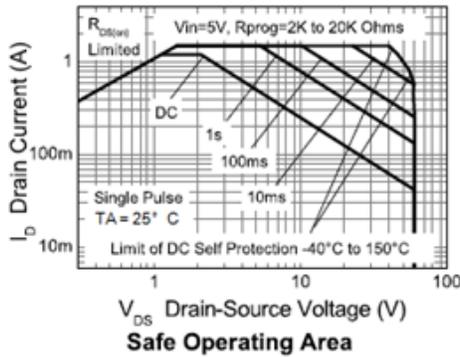
Electrical Characteristics (@T_A = +25°C, unless otherwise stated.)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Static Characteristics						
Drain-Source Clamp Voltage	$V_{DS(AZ)}$	60	70	75	V	I_D = 10mA
Off State Drain Current	I_{DSS}	—	0.1	3	µA	V_{DS} = 12V, V_{IN} = 0V
Off State Drain Current	I_{DSS}	—	3	15	µA	V_{DS} = 32V, V_{IN} = 0V
Input Threshold Voltage (Note 8)	$V_{IN(TH)}$	1	2.1	—	V	V_{DS} = V_{GS}, I_D = 1mA
Input Current	I_{IN}	—	0.7	1.2	mA	V_{IN} = 5V
Input Current	I_{IN}	—	1.5	2.7	mA	V_{IN} = 7V
Input Current	I_{IN}	—	4	7	mA	V_{IN} = 10V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	—	520	675	mΩ	V_{IN} = 5V, I_D = 0.2A
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	—	385	500	mΩ	V_{IN} = 10V, I_D = 0.5A
Current Limit (Note 9)	$I_{D(LIM)}$	0.2	0.3	0.4	A	V_{IN} = 5V, V_{DS} = 10V, R_{PROG} = 20k
Current Limit (Note 9)	$I_{D(LIM)}$	0.7	0.9	1.2	A	V_{IN} = 10V, V_{DS} = 10V, R_{PROG} = 20k
Dynamic Characteristics						
Turn-On Time (V_{IN} to 90% I_D)	t_{ON}	—	3	—	µs	R_{PROG} = 20k, R_L = 22Ω, V_{IN} = 0 to 10V, V_{DD} = 12V
Turn-Off Time (V_{IN} to 90% I_D)	t_{OFF}	—	13	—	µs	R_{PROG} = 20k, R_L = 22Ω, V_{IN} = 10V to 0V, V_{DD} = 12V
Slew Rate On (70 to 50% V_{DD})	dV_{DS}/dt_{ON}	—	8	—	V/µs	R_{PROG} = 20k, R_L = 22Ω, V_{IN} = 0 to 10V, V_{DD} = 12V
Slew Rate Off (50 to 70% V_{DD})	dV_{DS}/dt_{ON}	—	3.2	—	V/µs	R_{PROG} = 20k, R_L = 22Ω, V_{IN} = 10V to 0V, V_{DD} = 12V
Protection Functions (Note 10)						
Required Input Voltage for Over-Temperature Protection	V_{PROT}	4.5	—	—	V	—
Thermal Overload Trip Temperature	T_{JT}	+150	+175	—	°C	—
Thermal Hysteresis	—	—	+1	—	°C	—
Unclamped Single Pulse Inductive Energy T_J = +25°C	E_{AS}	550	—	—	mJ	$I_{D(ISO)}$ = 0.7A, V_{DD} = 32V
Unclamped Single Pulse Inductive Energy T_J = +150°C	E_{AS}	200	—	—	mJ	$I_{D(ISO)}$ = 0.7A, V_{DD} = 32V
Status Flag						
Normal Operation	V_{STATUS}	—	4.95	—	V	V_{IN} = 5V
Current Limit Operating	V_{STATUS}	—	2.5	—	V	V_{IN} = 5V
Thermal Shutdown Activated	V_{STATUS}	—	0.2	1	V	V_{IN} = 5V
Normal Operation	V_{STATUS}	—	8	—	V	V_{IN} = 10V
Current Limit Operation	V_{STATUS}	—	3	—	V	V_{IN} = 10V
Thermal Shutdown Activated	V_{STATUS}	—	0.35	1	V	V_{IN} = 10V
Inverse Diode						
Source Drain Voltage	V_{SD}	—	—	1	V	V_{IN} = 0V, -I_D = 1.4A

Notes: 8. Protection features may operate outside spec for V_{IN} < 4.5V.

9. The drain current is limited to a reduced value when V_{DS} exceeds a safe level.

10. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the datasheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous, repetitive operation.
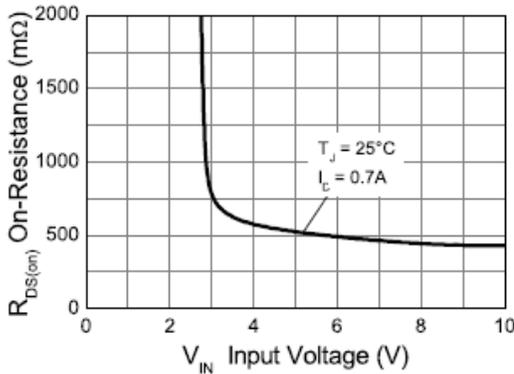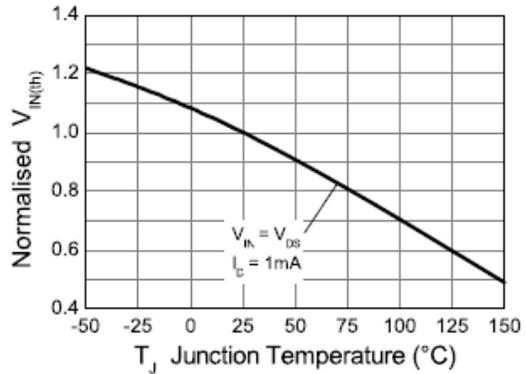
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Typical Characteristics
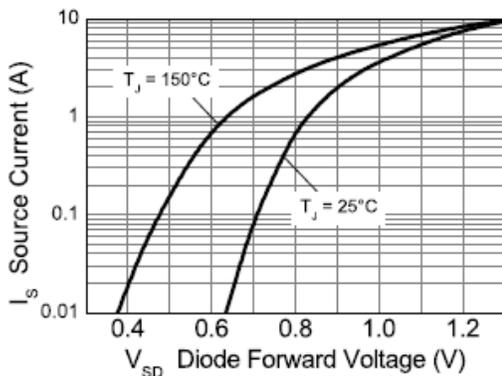
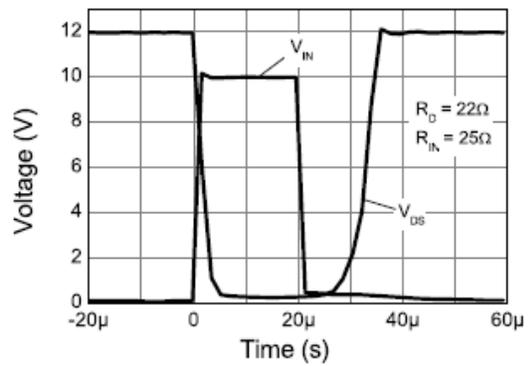**Typical Output Characteristic**
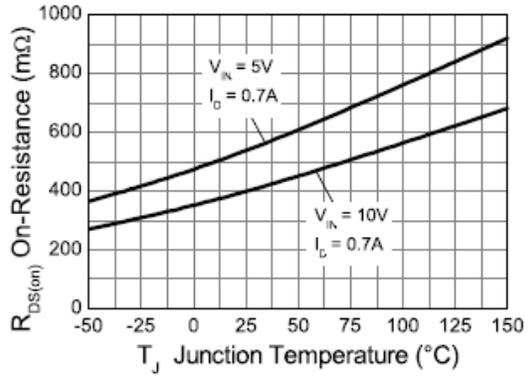
On-state Resistance vs Temperature

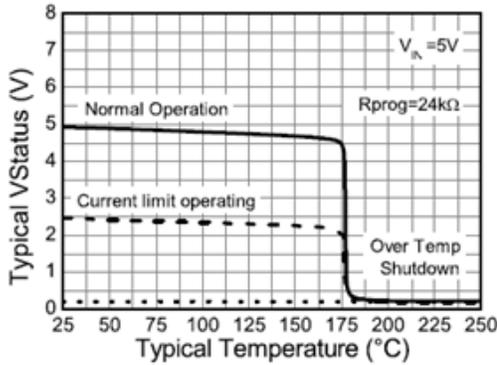**On-Resistance vs Input Voltage**

Threshold Voltage vs Temperature

Source-Drain Diode Forward Voltage

Switching Speed

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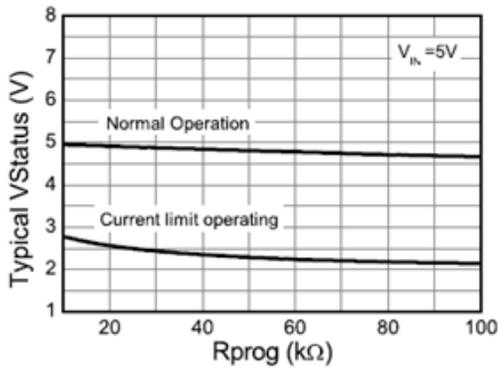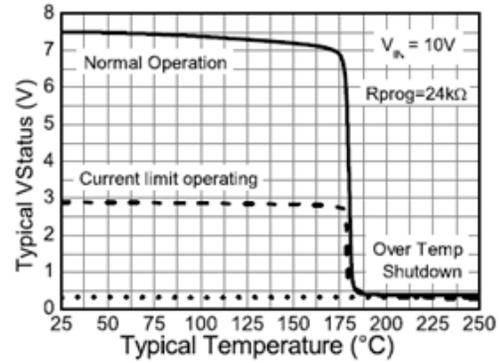
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Typical Characteristics (cont.)

Current Limiting and Over Temp Shutdown Status Indication at Vin=5V

Current Limiting and Over Temp Shutdown Status Indication at Vin=10V

VStatus vs Rprog @ Vin=5V
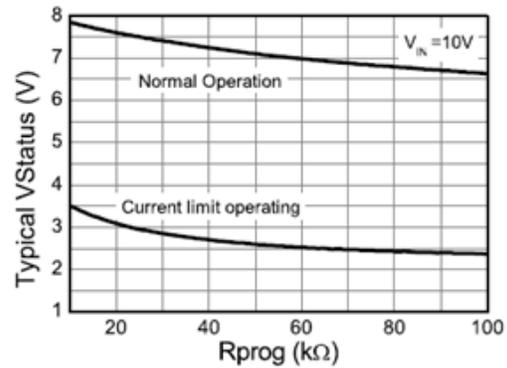
VStatus vs Rprog @ Vin=10V
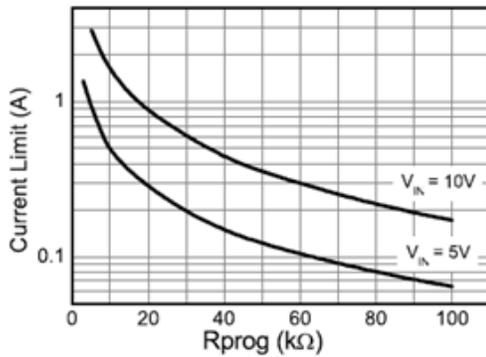
Current Limit vs Rprog

VStatus vs Vin

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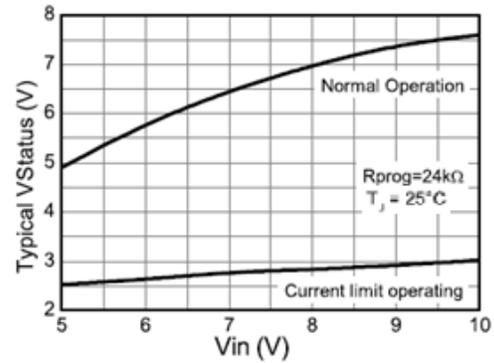
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.
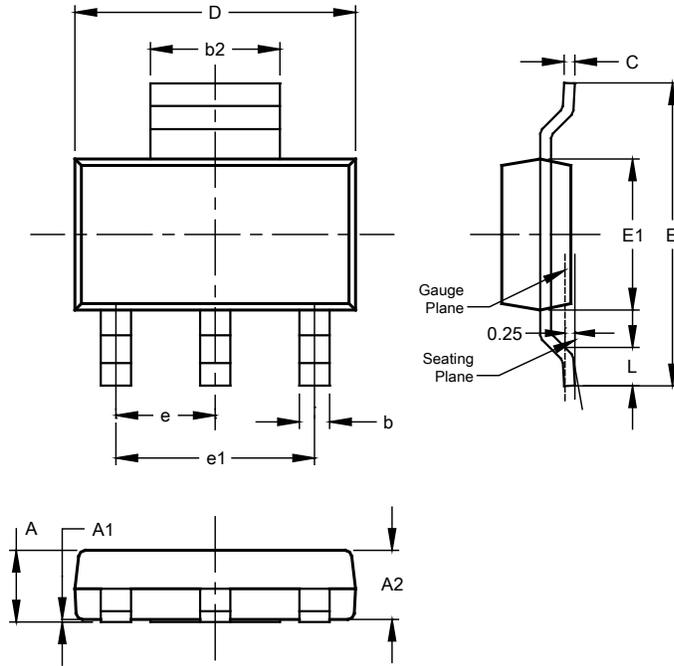
SOT223 (Type DN)

SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)
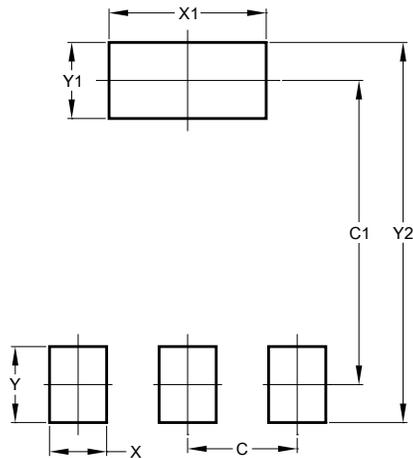
Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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